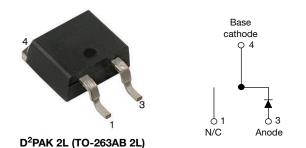
## **Vishay Semiconductors**

Hyperfast Rectifier, 30 A FRED Pt<sup>®</sup> G5



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### LINKS TO ADDITIONAL RESOURCES



| PRIMARY CHARACTERISTICS                    |                                     |  |  |  |  |  |  |  |
|--|-------------------------------------|--|--|--|--|--|--|--|
| I <sub>F(AV)</sub>                         | 30 A                                |  |  |  |  |  |  |  |
| V <sub>R</sub>                             | 600 V                               |  |  |  |  |  |  |  |
| V <sub>F</sub> at I <sub>F</sub> at 125 °C | 1.3 V                               |  |  |  |  |  |  |  |
| T <sub>J</sub> max.                        | 175 °C                              |  |  |  |  |  |  |  |
| t <sub>rr</sub> (typ.)                     | 22 ns                               |  |  |  |  |  |  |  |
| Package                                    | D <sup>2</sup> PAK 2L (TO-263AB 2L) |  |  |  |  |  |  |  |
| Circuit configuration                      | Single                              |  |  |  |  |  |  |  |

### **FEATURES**

- · Best in class forward voltage drop and switching losses trade off
- · Optimized for high speed operation
- 175 °C maximum operating junction temperature
- Polyimide passivation
- AEC-Q101 qualified, meets JESD 201 class 2 whisker test
- Meets MSL level, per J-Std-020, LF maximum peak of 245 °C
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912

### **DESCRIPTION / APPLICATIONS**

Featuring a unique combination of low conduction and switching losses, this rectifier is the right choice for soft switched and resonant converters, as well as medium frequency hard switching converters. This device is specifically designed to improve efficiency of high speed LLC output rectification stages of EV / HEV battery charging stations and high frequency stages of UPS applications.

### **MECHANICAL DATA**

Case: D<sup>2</sup>PAK 2L (TO-263AB 2L)

Molding compound meets UL 94 V-0 flammability rating

Terminals: matte tin plated leads, solderable per J-STD-002

| ABSOLUTE MAXIMUM RATINGS                   |                                   |   |             |       |  |  |  |  |  |  |
|--|-----------------------------------|---|-------------|-------|--|--|--|--|--|--|
| PARAMETER                                  | SYMBOL                            | TEST CONDITIONS                               | VALUES      | UNITS |  |  |  |  |  |  |
| Repetitive peak reverse voltage            | V <sub>RRM</sub>                  |   | 600         | V     |  |  |  |  |  |  |
| Average rectified forward current          | I <sub>F(AV)</sub>                | T <sub>C</sub> = 106 °C, D = 0.50             | 30          |       |  |  |  |  |  |  |
| Non-repetitive peak surge current          | I <sub>FSM</sub>                  | $T_C = 25$ °C, $t_p = 10$ ms, sine wave       | 310         | A     |  |  |  |  |  |  |
| Repetitive peak forward current            | I <sub>FRM</sub>                  | T <sub>C</sub> = 106 °C, D = 0.50, f = 20 kHz | 60          |       |  |  |  |  |  |  |
| Operating junction and storage temperature | T <sub>J</sub> , T <sub>Stg</sub> |   | -55 to +175 | °C    |  |  |  |  |  |  |

| <b>ELECTRICAL SPECIFICATIONS</b> (T <sub>J</sub> = 25 °C unless otherwise specified) |                                     |   |      |      |      |       |  |  |  |  |
|--|-------------------------------------|---|------|------|------|-------|--|--|--|--|
| PARAMETER  | SYMBOL                              | TEST CONDITIONS                                 | MIN. | TYP. | MAX. | UNITS |  |  |  |  |
| Breakdown voltage, blocking voltage  | V <sub>BR</sub> ,<br>V <sub>R</sub> | I <sub>R</sub> = 100 μA                         | 600  | -    | -    |       |  |  |  |  |
|  | V <sub>F</sub>                      | I <sub>F</sub> = 30 A                           | -    | 1.6  | 2.1  | V     |  |  |  |  |
| Forward voltage  |                                     | I <sub>F</sub> = 30 A, T <sub>J</sub> = 125 °C  | -    | 1.3  | -    |       |  |  |  |  |
| Poweree leekage eurrent  | I <sub>R</sub>                      | $V_{R} = V_{R}$ rated                           | -    | -    | 20   |       |  |  |  |  |
| Reverse leakage current  |                                     | $T_J = 125 \text{ °C}, V_R = V_R \text{ rated}$ | -    | -    | 500  | μA    |  |  |  |  |
| Junction capacitance   | CT                                  | V <sub>R</sub> = 200 V                          | -    | 36   | -    | pF    |  |  |  |  |
| Series inductance  | L <sub>S</sub>                      | Measured to lead 5 mm from package body         | -    | 8    | -    | nH    |  |  |  |  |

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# Vishay Semiconductors

| <b>DYNAMIC RECOVERY CHARACTERISTICS</b> ( $T_J = 25$ °C unless otherwise specified) |                  |  |  |      |      |       |    |  |  |  |
|---|------------------|--|--|------|------|-------|----|--|--|--|
| PARAMETER   | SYMBOL           | TEST CO                                      | MIN.   | TYP. | MAX. | UNITS |    |  |  |  |
|   |                  | I <sub>F</sub> = 1.0 A,dI <sub>F</sub> /dt = | 100 A/µs, V <sub>R</sub> = 30 V                          | -    | 22   | -     |    |  |  |  |
| Reverse recovery time   | t <sub>rr</sub>  | T <sub>J</sub> = 25 °C                       |  | -    | 39   | -     | ns |  |  |  |
|   |                  | T <sub>J</sub> = 125 °C                      |  | -    | 50   | -     |    |  |  |  |
| Peak recovery current   |                  | T <sub>J</sub> = 25 °C                       | I <sub>F</sub> = 20 A<br>dI <sub>F</sub> /dt = 1000 A/µs | -    | 14   | -     | A  |  |  |  |
|   | IRRM             | T <sub>J</sub> = 125 °C                      | $V_{\rm R} = 400 \text{ V}$                              | -    | 24   | -     |    |  |  |  |
| Davience in a construction of a mark  | Q <sub>rr</sub>  | T <sub>J</sub> = 25 °C                       |  | -    | 253  | -     | nC |  |  |  |
| Reverse recovery charge   |                  | T <sub>J</sub> = 125 °C                      |  | -    | 785  | -     |    |  |  |  |
| Reverse recovery time   | t <sub>rr</sub>  | T <sub>J</sub> = 25 °C                       |  | -    | 41   | -     | ns |  |  |  |
| neverse recovery time   |                  | T <sub>J</sub> = 125 °C                      |  | -    | 56   | -     |    |  |  |  |
| Peak recovery current   | 1                | T <sub>J</sub> = 25 °C                       | I <sub>F</sub> = 30 A<br>dI <sub>F</sub> /dt = 1000 A/µs | -    | 16   | -     | A  |  |  |  |
| reak recovery current   | I <sub>RRM</sub> | T <sub>J</sub> = 125 °C                      | $V_{\rm R} = 400  \text{V}$                              | -    | 27   | -     |    |  |  |  |
| Deverse we are a strained   | 0                | T <sub>J</sub> = 25 °C                       | ]  | -    | 306  | -     |    |  |  |  |
| Reverse recovery charge   | Q <sub>rr</sub>  | T <sub>J</sub> = 125 °C                      |  | -    | 952  | -     | nc |  |  |  |

| THERMAL - MECHANICAL SPECIFICATIONS            |                                   |  |            |      |      |       |  |  |  |  |  |
|--|-----------------------------------|--|------------|------|------|-------|--|--|--|--|--|
| PARAMETER                                      | SYMBOL                            | TEST CONDITIONS                                    | MIN.       | TYP. | MAX. | UNITS |  |  |  |  |  |
| Thermal resistance, junction-to-case           | R <sub>thJC</sub>                 |  | -          | -    | 1.3  | °C/W  |  |  |  |  |  |
|  |                                   |  | -          | 2.0  | -    | g     |  |  |  |  |  |
| Weight   |                                   |  | -          | 0.07 | -    | oz.   |  |  |  |  |  |
| Maximum junction and storage temperature range | T <sub>J</sub> , T <sub>Stg</sub> |  | -55        | -    | 175  | °C    |  |  |  |  |  |
| Marking device                                 |                                   | Case style:<br>D <sup>2</sup> PAK 2L (TO-263AB 2L) | E5TX3006SH |      |      |       |  |  |  |  |  |



## **VS-E5TX3006S2LHM3**

## **Vishay Semiconductors**

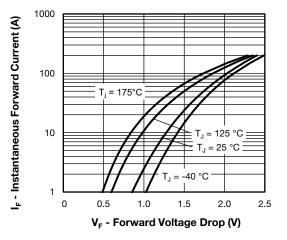


Fig. 1 - Typical Forward Voltage Drop Characteristics

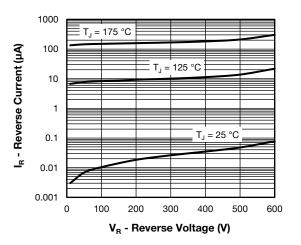


Fig. 2 - Typical Values of Reverse Current vs. Reverse Voltage

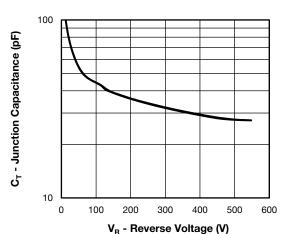
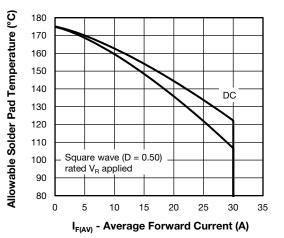
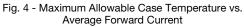


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage





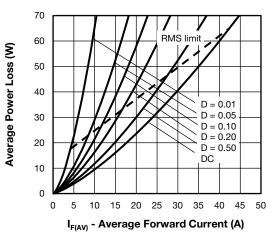


Fig. 5 - Average Power Loss vs. Average Forward Current

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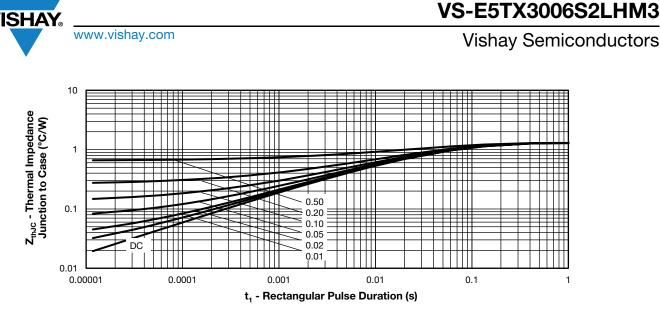


Fig. 6 - Thermal Impedance ZthJC - Characteristics

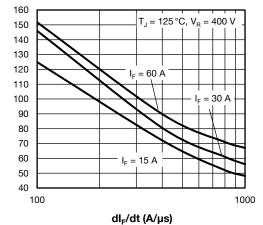


Fig. 7 - Typical Reverse Recovery Time vs. dI<sub>F</sub>/dt

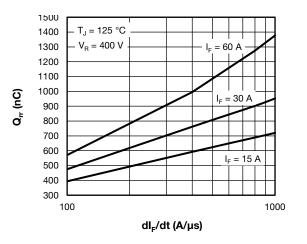


Fig. 8 - Typical Reverse Recovery Charge vs. dl<sub>F</sub>/dt

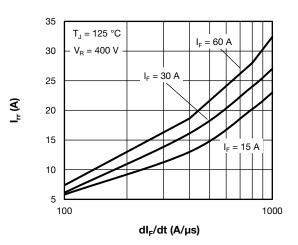


Fig. 9 - Typical Reverse Recovery Current vs. dl<sub>F</sub>/dt

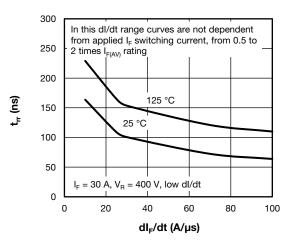


Fig. 10 - Typical Reverse Recovery Time vs. dl<sub>F</sub>/dt

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# VS-E5TX3006S2LHM3

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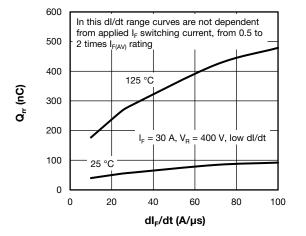


Fig. 11 - Typical Reverse Recovery Charge vs. dl<sub>F</sub>/dt

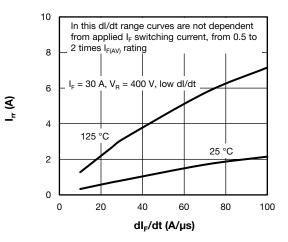


Fig. 12 - Typical Reverse Recovery Current vs. dl<sub>F</sub>/dt

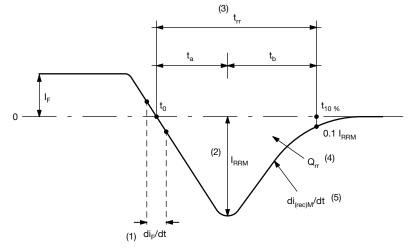


Fig. 13 - Reverse Recovery Waveform and Definitions

#### Notes

- $^{(1)}$  di<sub>F</sub>/dt rate of change of current through zero crossing
- <sup>(2)</sup> I<sub>RRM</sub> peak reverse recovery current
- $^{(3)}$  t<sub>rr</sub> reverse recovery time measured from t<sub>0</sub>, crossing point of negative going I<sub>F</sub>, to point t<sub>10%</sub>, 0.1 I<sub>RRM</sub>
- $^{(4)}~~Q_{rr}$  area under curve defined by  $t_0$  and  $t_{10}~\%$

$$Q_{rr} = \int_{t_r}^{t_{10}\%} I(t)dt$$

 $^{(5)}$  di<sub>(rec)</sub>M/dt - peak rate of change of current during t<sub>b</sub> portion of t<sub>rr</sub>

## Vishay Semiconductors



| Device code | VS-   | Е                            | 5 | т                       | x | 30      | 06       | S2      | L         | н        | М3   |
|-------------|---|------------------------------|---|-------------------------|---|---------|----------|---------|-----------|----------|------|
|             | 1   | 2                            | 3 | 4                       | 5 | 6       | 7        | 8       | 9         | 10       | (11) |
|             | <ul> <li>Vishay Semiconductors product</li> <li>E = single diode</li> </ul>   |                              |   |                         |   |         |          |         |           |          |      |
|             | <ul> <li>3 - 5 = FRED generation 5</li> <li>4 - Package:<br/>T = D<sup>2</sup>PAK (TO-262) package</li> </ul>   |                              |   |                         |   |         |          |         |           |          |      |
|             | 6   | - Current rating (30 = 30 A) |   |                         |   |         |          |         |           |          |      |
|             | <ul> <li>7 - Voltage rating (06 = 600 V)</li> <li>8 - S2 = true 2 pin D<sup>2</sup>PAK</li> </ul>   |                              |   |                         |   |         |          |         |           |          |      |
|             | <ul> <li>9 - None = tube (50 pieces)</li> <li>• L = tape and reel (left oriented, for D<sup>2</sup>PAK package)<br/>If needed different orientation/packaging, please contact factory</li> <li>10 - H = AEC-Q101 qualified</li> </ul> |                              |   |                         |   |         |          |         |           |          |      |
|             |   |                              |   | ntal digit<br>jen-free, |   | complia | ant, and | termina | ation lea | d (Pb)-f | ree  |

| ORDERING INFORMATION (Example) |                       |  |  |  |  |  |  |
|--------------------------------|-----------------------|--|--|--|--|--|--|
| BASE QUANTITY                  | PACKAGING DESCRIPTION |  |  |  |  |  |  |
| 800                            | 13" diameter reel     |  |  |  |  |  |  |
|                                | BASE QUANTITY         |  |  |  |  |  |  |

| LINKS TO RELATED DOCUMENTS |                          |  |  |  |  |  |  |
|----------------------------|--------------------------|--|--|--|--|--|--|
| Dimensions                 | www.vishay.com/doc?96683 |  |  |  |  |  |  |
| Part marking information   | www.vishay.com/doc?96693 |  |  |  |  |  |  |
| Packaging information      | www.vishay.com/doc?95032 |  |  |  |  |  |  |
| SPICE model                | www.vishay.com/doc?96918 |  |  |  |  |  |  |

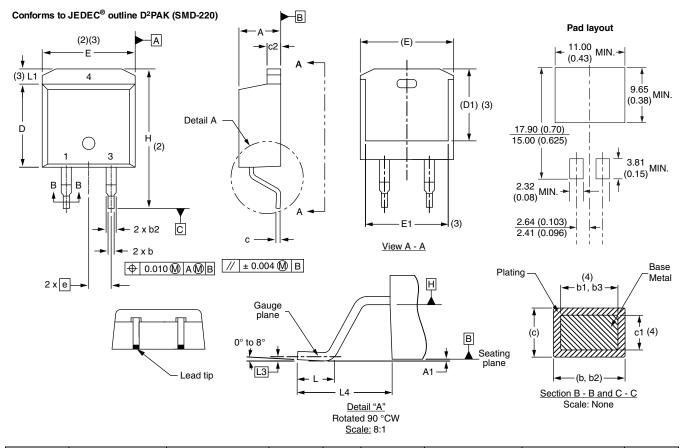
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**Vishay Semiconductors** 



D<sup>2</sup>PAK 2L (TO-263AB 2L)

### **DIMENSIONS** in millimeters and inches



| SYMBOL | MILLIMETERS |       | INCHES |       | NOTES | , NOTES               |        | SYMBOL   | MILLIM | IETERS    | INC   | HES   | NOTES |
|--------|-------------|-------|--------|-------|-------|-----------------------|--------|----------|--------|-----------|-------|-------|-------|
| STMBOL | MIN.        | MAX.  | MIN.   | MAX.  | NOTES | NOTES                 | STWDUL | MIN.     | MAX.   | MIN.      | MAX.  | NOTES |       |
| А      | 4.06        | 4.83  | 0.160  | 0.190 |       |                       | D1     | 6.86     | 8.00   | 0.270     | 0.315 | 3     |       |
| A1     | 0.00        | 0.254 | 0.000  | 0.010 |       |                       | Е      | 9.65     | 10.67  | 0.380     | 0.420 | 2, 3  |       |
| b      | 0.51        | 0.99  | 0.020  | 0.039 |       |                       | E1     | 7.90     | 8.80   | 0.311     | 0.346 | 3     |       |
| b1     | 0.51        | 0.89  | 0.020  | 0.035 | 4     |                       | е      | 2.54 BSC |        | 0.100 BSC |       |       |       |
| b2     | 1.14        | 1.78  | 0.045  | 0.070 |       |                       | Н      | 14.61    | 15.88  | 0.575     | 0.625 |       |       |
| b3     | 1.14        | 1.73  | 0.045  | 0.068 | 4     |                       | L      | 1.78     | 2.79   | 0.070     | 0.110 |       |       |
| с      | 0.38        | 0.74  | 0.015  | 0.029 |       |                       | L1     | -        | 1.65   | -         | 0.066 | 3     |       |
| c1     | 0.38        | 0.58  | 0.015  | 0.023 | 4     | L3 0.25 BSC 0.010 BSC |        | 0.25 BSC |        | BSC       |       |       |       |
| c2     | 1.14        | 1.65  | 0.045  | 0.065 |       |                       | L4     | 4.78     | 5.28   | 0.188     | 0.208 |       |       |
| D      | 8.51        | 9.65  | 0.335  | 0.380 | 2     |                       |        |          |        |           |       |       |       |

#### Notes

<sup>(1)</sup> Dimensioning and tolerancing per ASME Y14.5 M-1994

(2) Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outmost extremes of the plastic body
 (3) Thermal and contain antional within dimension E 1.1, D1 and E1.

<sup>(3)</sup> Thermal pad contour optional within dimension E, L1, D1 and E1

<sup>(4)</sup> Dimension b1 and c1 apply to base metal only

<sup>(5)</sup> Datum A and B to be determined at datum plane H

<sup>(6)</sup> Controlling dimension: inch

(7) Outline conforms to JEDEC® outline TO-263AB

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